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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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HD74CBT3345

8-bit FET Bus Switch

ADE-205-644 (Z)

Preliminary
Rev. 0
August 2001

Description

The HD74CBT3345 provides eight bits of high speed TTL-compatible bus switching in a standard ’245 device pinout. The low on state resistance of the switch allows connections to be made with minimal propagation delay. The device is organized as one 8-bit switch bank with dual output enable (OE and $\overline{OE}$) inputs. When $\overline{OE}$ is low or OE is high, the switch is on, and port A is connected to port B. When $\overline{OE}$ is high and OE is low, the switch is open, and the high impedance state exists between the two ports.

Features

- Standard ’245 type pinout.
- Minimal propagation delay through the switch.
- 5 Ω switch connection between two ports.
- TTL-compatible input levels.
- Ultra low quiescent power.
  -Ideally suited for notebook applications.

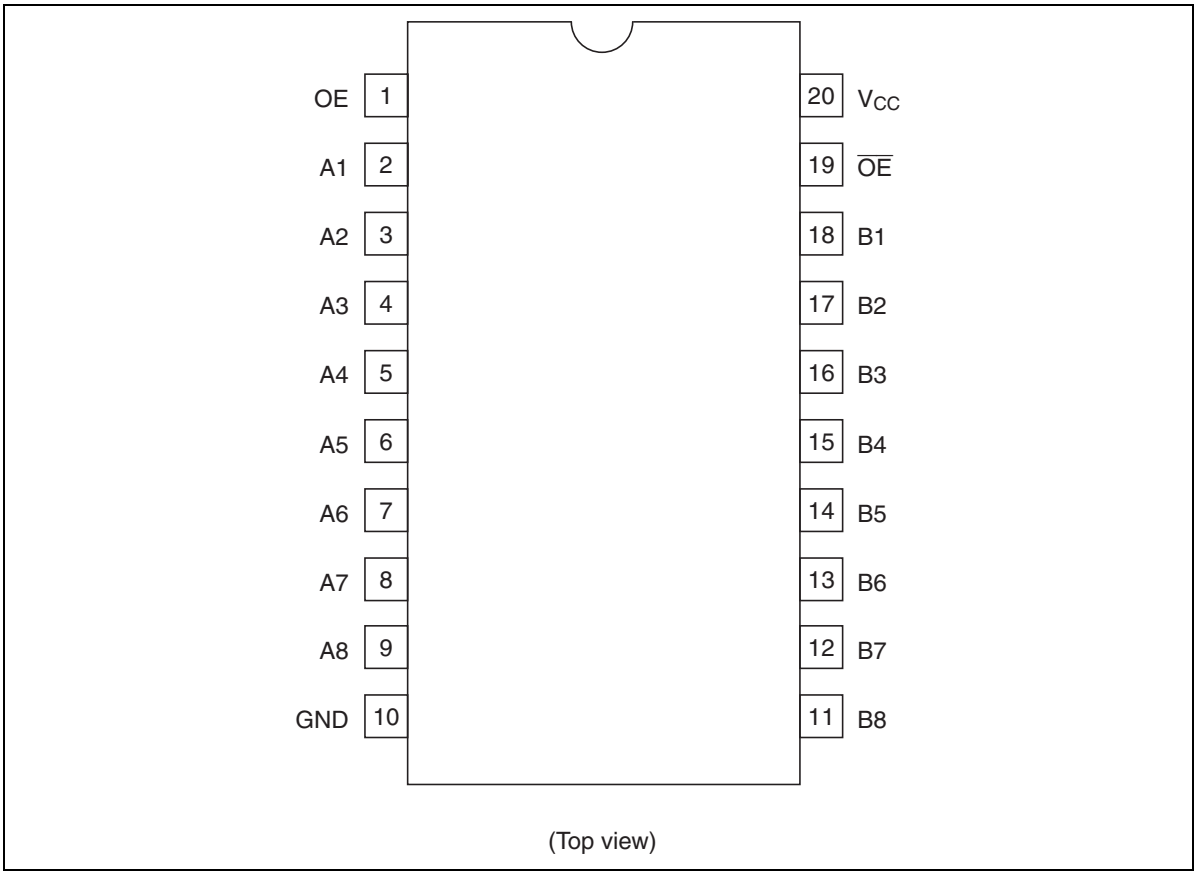
Function Table

Inputs

$\overline{OE}$	OE	Function
L	X	A port = B port
X	H	A port = B port
H	L	Disconnect

H: High level
L: Low level
X: Immaterial

Pin Arrangement



(Top view)

Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Conditions
Supply voltage range	V_{CC}	–0.5 to 7.0	V	
Input voltage range [*1]	V_I	–0.5 to 7.0	V	
Input clamp current	I_{IK}	–50	mA	$V_I < 0$
Continuous output current	I_O	128	mA	V_O = 0 to V_{CC}
Continuous current through V_{CC} or GND	I_{CC} or I_{GND}	±100	mA	
Maximum power dissipation at Ta = 25°C (in still air) [*2]	P_T	757	mW	TSSOP
Storage temperature	Tstg	–65 to 150	°C	

Notes: The absolute maximum ratings are values which must not individually be exceeded, and furthermore, no two of which may be realized at the same time.

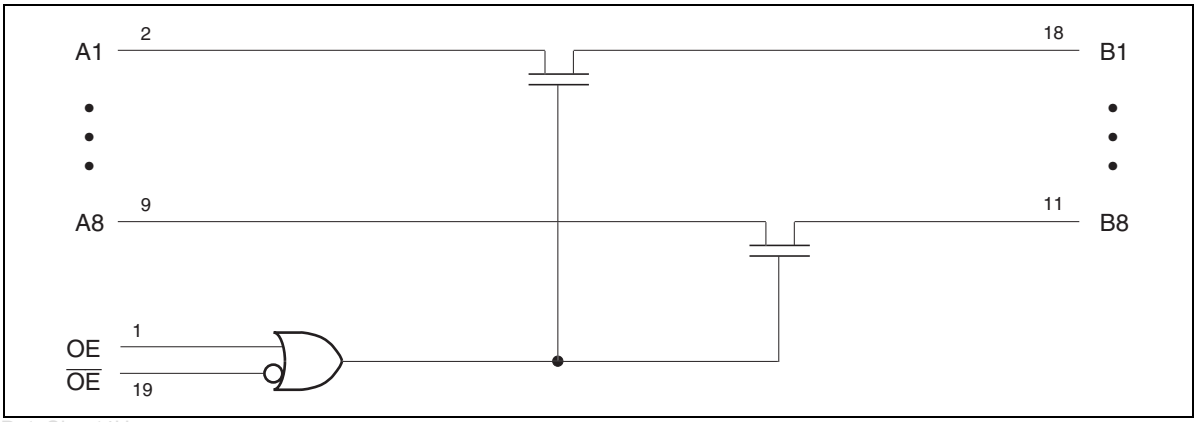
1. The input and output voltage ratings may be exceeded even if the input and output clamp-current ratings are observed.
2. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V_{CC}	4.5	5.5	V	
Input voltage range	V_I	0	5.5	V	
Output voltage range	$V_{I/O}$	0	5.5	V	
Input transition rise or fall rate	$\Delta t / \Delta v$	0	5	ns / V	V_{CC} = 4.5 to 5.5 V
Operating free-air temperature	Ta	–40	85	°C	

Note: Unused or floating inputs must be held high or low.

Block Diagram



DC Electrical Characteristics

(Ta = –40 to 85°C)

Item	Symbol	V_{CC} (V)	Min	Typ [*1]	Max	Unit	Test conditions
Clamp diode voltage	V_{IK}	4.5	—	—	–1.2	V	I_{IN} = –18 mA
Input voltage	V_{IH}	4.5 to 5.5	2.0	—	—	V	
	V_{IL}	4.5 to 5.5	—	—	0.8		
On-state switch resistance [*2]	R_{ON}	4.5	—	5	7	Ω	V_{IN} = 0 V, I_{IN} = 64 mA
		4.5	—	5	7		V_{IN} = 0 V, I_{IN} = 30 mA
		4.5	—	10	15		V_{IN} = 2.4 V, I_{IN} = 15 mA
Input current	I_{IN}	0 to 5.5	—	—	±1.0	µA	V_{IN} = 5.5 V or GND
Off-state leakage current	I_{OZ}	5.5	—	—	±1.0	µA	0 ≤ A, B ≤ V_{CC}
Quiescent supply current	I_{CC}	5.5	—	—	3	µA	V_{IN} = V_{CC} or GND, I_O = 0 mA
Increase in I_{CC} per input [*3]	ΔI_{CC}	5.5	—	—	2.5	mA	One input at 3.4 V, other inputs at V_{CC} or GND

Notes: For condition shown as Min or Max use the appropriate values under recommended operating conditions.

1. All typical values are at V_{CC} = 5 V (unless otherwise noted), Ta = 25°C.
2. Measured by the voltage drop between the A and B terminals at the indicated current through the switch. On-state resistance is determined by the lower voltage of the two (A or B) terminals.
3. This is the increase in supply current for each input that is at the specified TTL voltage level rather than V_{CC} or GND.

Capacitance

(Ta = 25°C)

Item	Symbol	V_{CC} (V)	Min	Typ	Max	Unit	Test conditions
Control input capacitance	C_{IN}	5.0	—	3.5	—	pF	V_{IN} = 0 or 3 V
Input / output capacitance	$C_{I/O (OFF)}$	5.0	—	5	—	pF	V_O = 0 or 3 V, $\overline{OE}$ = V_{CC}

Note: This parameter is determined by device characterization is not production tested.

Switching Characteristics

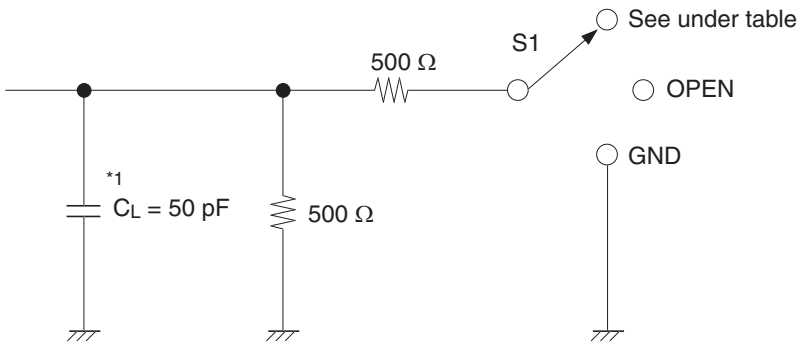
(Ta = –40 to 85°C)

- V_{cc} = 5.0±0.5 V

Item	Symbol	Min	Max	Unit	Test conditions	FROM (Input)	TO (Output)
Propagation delay time [*1]	t_{PLH} t_{PHL}	—	0.25	ns	C_L = 50 pF R_L = 500 Ω	A or B	B or A
Enable time	t_{ZH} t_{ZL}	1.0	9.1	ns	C_L = 50 pF R_L = 500 Ω	$\overline{OE}$	A or B
Disable time	t_{HZ} t_{LZ}	1.0	8.7	ns	C_L = 50 pF R_L = 500 Ω	$\overline{OE}$	A or B

Note: 1. The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance, when driven by an ideal voltage source (zero output impedance).

Test Circuit

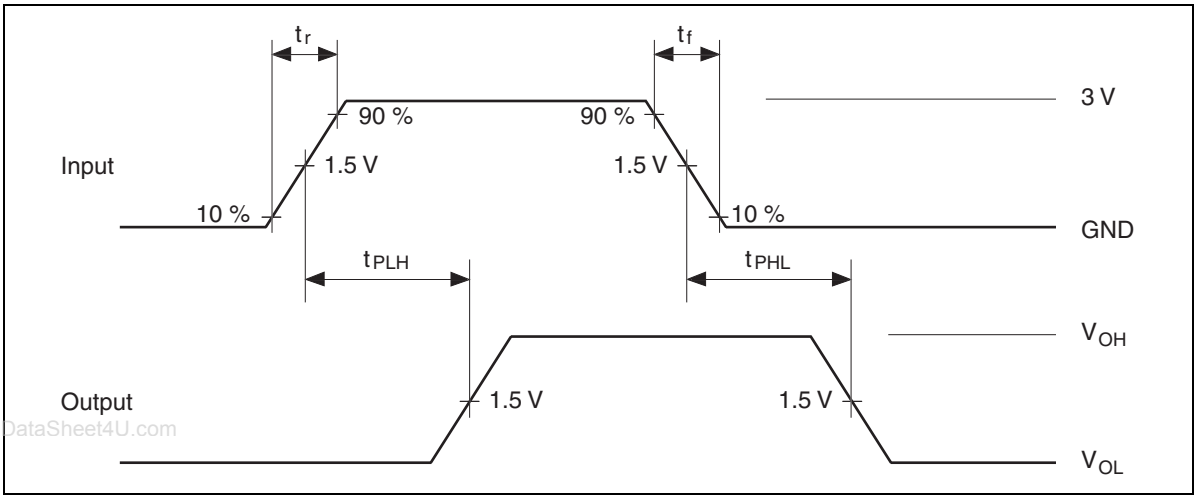


Load circuit for outputs

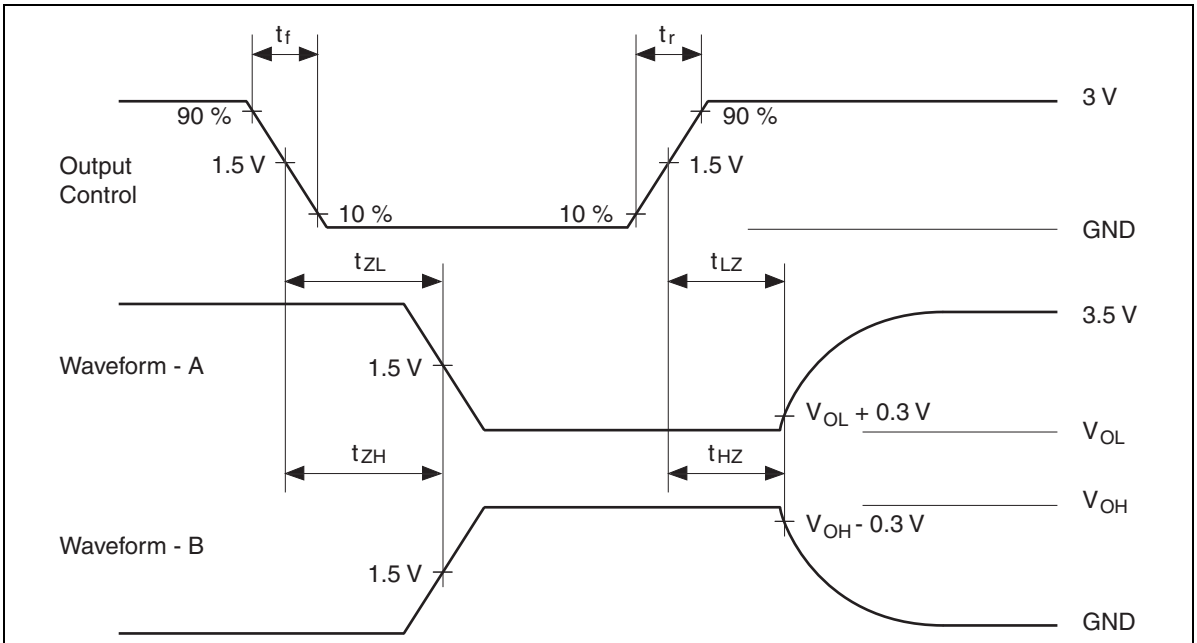
Symbol	S1
t_{PLH}/ t_{PHL}	OPEN
t_{ZH} / t_{HZ}	OPEN
t_{ZL} / t_{LZ}	7 V

Note: 1. C_L includes probe and jig capacitance.

Waveforms – 1



Waveforms – 2

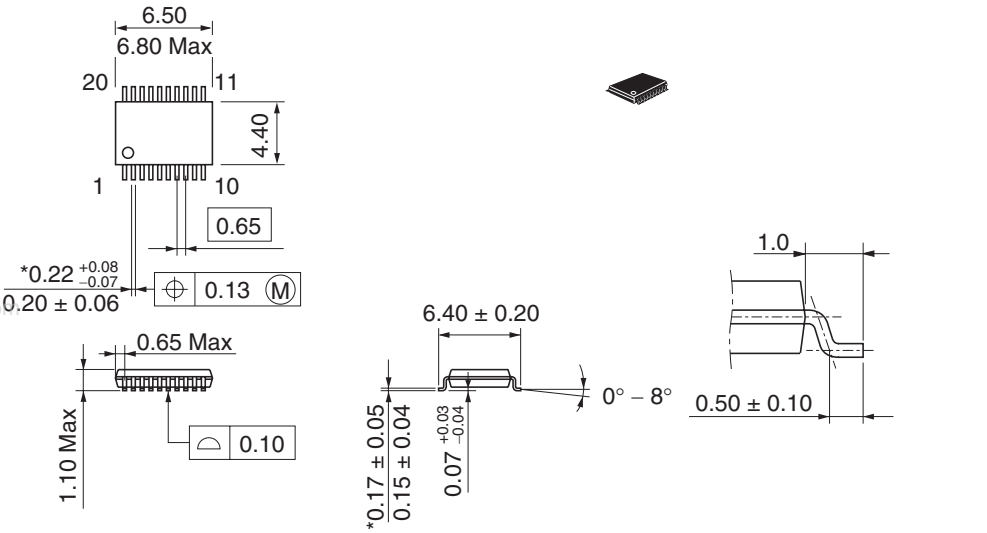


Notes: 1. All input pulses are supplied by generators having the following characteristics : PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2.5 ns, t_f ≤ 2.5 ns.
2. Waveform - A is for an output with internal conditions such that the output is low except when disabled by the output control.
3. Waveform - B is for an output with internal conditions such that the output is high except when disabled by the output control.
4. The output are measured one at a time with one transition per measurement.

Package Dimensions

As of January, 2001

Unit: mm



*Dimension including the plating thickness

Base material dimension

Hitachi Code	TTP-20DA
JEDEC	—
EIAJ	—
Mass (reference value)	0.07 g

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